

# YJ Planar Schottky Barrier Diode Die Specification

30V 0.5A, 25mil, Schottky barrier diode die based on silicon planar process  
Part No.: PSB025L030AS-180A

## Main Products Characteristics

Reverse current  $I_R$  at  $V_R = 30V$  and  $T_a = 25^\circ C$  is  $I_R \leq 10\mu A$   
Forward voltage drop  $V_F$  at  $I_F = 0.5A$  and  $T_a = 25^\circ C$  is  $V_F \leq 0.6V$   
Forward voltage drop  $V_F$  at  $I_F = 0.5A$  and  $T_a = 100^\circ C$  is  $V_F \leq 0.7V$

## Maximum Ratings

## Static Electrical Characteristics (Ta = 25°C)

$I_F = 0.5A$

Reverse current  $I_R$  at  $V_R = 30V$  is  $I_R \leq 10\mu A$  ± 2%

## Device Schematics and Outline Drawing

Die Thickness \*

Die Size \*\*

Top Metal  $\leq 0.05\mu m$